AMENDMENTS

In the Specification:

On page 1, under BACKGROUND OF THE INVENTION, please insert the following paragraph:

--CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims priority to Japanese Patent Application Number 2001-050558 filed February 26, 2001, and Japanese Patent Application Number 2002-41913 filed February 19, 2002, the contents of which are incorporated herein by reference in their entireties.--

In the Claims:

Please amend claims 4, 6, 8, and 10 as follows:

Please add new claims 12-27.

4. (Amended) A light-emitting diode claimed in Claim 1, wherein the light reflecting layer is formed of a metal thin film.

6. (Amended) A light-emitting diode claimed in Claim 4, wherein the metal thin film is formed of an Ni vapor-deposition film.

8. (Amended) A light-emitting diode claimed in Claim 1, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

10. (Amended) A light-emitting diode claimed in Claim 1, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

Please add new claims 12-27

12. (New) A light-emitting diode claimed in Claim 2, wherein the light reflecting layer is formed of a metal thin film.

13. (New) A light-emitting diode claimed in Claim 5, wherein the metal thin film is formed of an Ni vapor-deposition film.

14. (New) A light-emitting diode claimed Claim 2, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

15. (New) A light-emitting diode claimed in Claim 3, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

16. (New) A light-emitting diode claimed in Claim 4, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

17. (New) A light-emitting diode claimed in Claim 5, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

18. (New) A light-emitting diode claimed in Claim 6, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

19. (New) A light-emitting diode claimed in Claim 7, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

20. (New) A light-emitting diode claimed in Claim 2, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

21. (New) A light-emitting diode claimed in Claim 3, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

22. (New) A light-emitting diode claimed in Claim 4, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

23. (New) A light-emitting diode claimed in Claim 5, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

24. (New) A light-emitting diode claimed in Claim 6, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

25. (New) A light-emitting diode claimed in Claim 7, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

26. (New) A light-emitting diode claimed in Claim 8, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

27. (New) A light-emitting diode claimed in Claim 9, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.